

1. (Amended) A semiconductor device comprising:

A1 a first portion comprising a first substrate, a conductive layer and an insulating layer laminated on the first substrate and a bonding surface that is chemically mechanically polished and exposes a conductive region and an insulating region, wherein the conductive region includes a concave surface defining a dishing portion;

a second portion comprising a second substrate, a conductive layer and an insulating layer laminated on the second substrate and a bonding surface that is chemically mechanically polished and exposes at least a conductive region having a concave surface defining a dishing portion; and wherein

the bonding surface of the first portion and the bonding surface of the second portion are solid-state-bonded to each other so that the dishing portions of the conductive regions of the respective first and second portions are bonded to each other so as to contact one another, and

at least one of the bonding surface of the first portion and the bonding surface of the second portion has the insulating region lowered with respect to the conductive region.

Please add the following new claims:

A2 20. (New) A semiconductor device comprising:

a first substrate supporting a first insulating layer with a contact hole defined therein, and a first conductive material filling in the contact hole in the first insulating layer and protruding above a surface of the first insulating layer;

a second substrate supporting a second insulating layer with a contact hole defined therein, and a second conductive material filling in the contact hole in the second insulating layer; and

wherein the first conductive material that fills in the contact hole in the first insulating layer and the second conductive material that fills in the contact hole in the second insulating layer are solid-state-bonded to each other so as to contact one another in a bonded state.

A2
CONT.

21. (New) The semiconductor device of claim 20, wherein the second conductive material filling in the contact hole in the second insulating layer protrudes above a surface of the second insulating layer.

22. (New) The semiconductor device of claim 20, wherein the first and second conductive materials are of the same material.

23. (New) The semiconductor device of claim 20, wherein concave surfaces of the respective first and second conductive materials are bonded to one another so as to contact each other.